

SEMICONDUCTOR®

DUAL PHOTOTRANSISTOR OPTOCOUPLERS

MCT9001

DESCRIPTION

The MCT9001 Optocoupler has two channels for density applications. For four channel applications, two-packages fit into a standard 16-pin DIP socket. Each channel is an NPN silicon planar phototransistor optically coupled to a gallium arsenide infrared emitting diode.

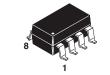
FEATURES

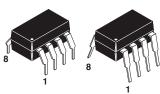
- Two isolated channels per package
- · Two packages fit into a 16 lead DIP socket
- Underwriters Laboratory (U.L.) recognized File E90700

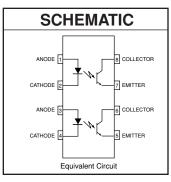
APPLICATIONS

- · AC Line/Digital Logic isolate high voltage transients
- · Digital Logic/Digital Logic Eliminate spurious grounds
- Digital Logic/AC Triac Control isolate high voltage transients
- Twisted pair line receiver Eliminate ground loop feedthrough
- · Telephone/Telegraph line receiver isolate high voltage transients
- High Frequency Power Supply Feedback Control Maintain floating grounds and transients
- · Relay contact monitor isolate floating grounds and transients
- · Power supply monitor Isolate transients

ABSOLUTE MAXIMUM RATINGS				
Rating	Symbol	Value	Unit	
EMITTER (Each channel)				
Forward Current - Continuous	I _F	60	mA	
Forward Current - Peak (PW = 1µs, 300pps)	I _F (pk)	3	A	
Reverse Voltage	V _R	5.0	V	
LED Power Dissipation @ T _A = 25°C Derate above 25°C (Total Input)	P _D	100 1.1	mW mW/°C	
DETECTOR (Each channel)				
Collector Current - Continuous	Ι _C	30	mA	
Detector Power Dissipation @ T _A = 25°C Derate above 25°C	P _D	150 1.67	mW mW/°C	
TOTAL DEVICE				
Storage Temperature	T _{STG}	-55 to +150	°C	
Operating Temperature	T _{OPR}	-55 to +100	٥C	
Lead Solder Temperature	T _{SOL}	250 for 10 sec	°C	
Total Device Power Dissipation @ T _A = 25°C Derate above 25°C	P _D	400 4.83	mW mW/°C	







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ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ Unless otherwise specified.)						
INDIVIDUAL COMPONENT CHARACTERISTICS						
Parameter	Test Conditions	Symbol	Min	Тур**	Max	Unit
EMITTER						
Input Forward Voltage	(I _F = 10 mA)	V _F		1.0	1.3	V
Reverse Current	(V _R = 5 V)	I _R			10	μA
Junction Capacitance	(V _F = 0 V, f = 1 MHz)	CJ		50		pF
DETECTOR						
Collector-Emitter Breakdown Voltage	$(I_{C} = 0.5 \text{ mA}, I_{F} = 0)$	BV _{CEO}	55			V
Emitter-Collector Breakdown Voltage	(I _E = 100 µA, I _F = 0)	BV _{ECO}	7			V
Collector-Emitter Dark Current —	$(V_{CE} = 24 \text{ V}, I_F = 0)$	1		5	100	nA
	$(V_{CE} = 24 \text{ V}, \text{T}_{A} = 85^{\circ}\text{C})$	ICEO			50	μA
Capacitance	(V _{CE} = 0 V, f = 1 MHz)	C _{CE}		8		pF

TRANSFER CHARACTERISTICS						
AC Characteristic	Test Conditions	Symbol	Min	Тур**	Max	Units
SWITCHING TIMES						
Non-Saturated						
Turn-on Time		t _{on}		3		
Turn-off Time		t _{off}		3		
Rise Time	$(R_L = 100 \Omega, I_C = 2 mA, V_{CC} = 10 V)$	t _r		2.4		μs
Fall Time		t _f		2.4		
Saturated						
Turn-on Time	(I = 16 mA P = 1.9 kO V = 5 V)	t _{on}		2.4		
Turn-off Time	$(I_F = 16 \text{ mA}, \text{ R}_L = 1.9 \text{ k}\Omega, \text{ V}_{CE} = 5 \text{ V})$	t _{off}		25.0		1

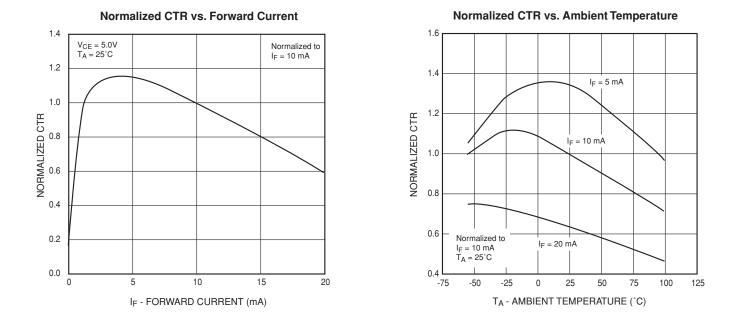
TRANSFER CHARACTERISTICS						
DC Characteristic	Test Conditions	Symbol	Min	Тур**	Мах	Units
Current Transfer Datia Callector Emitter	(I _F = 5 mA, V _{CE} = 5 V)	CTR	50		600	%
Current Transfer Ratio, Collector-Emitter	$(I_F = 8 \text{ mA}, V_{CE} = 0.4 \text{ V})$	CTR _(sat)	30			/0
Saturation Voltage	$(I_F = 8 \text{ mA}, I_C = 2.4 \text{ mA})$	V _{CE(sat)}			0.40	V

ISOLATION CHARACTERIS	TICS					
Characteristic	Test Conditions	Symbol	Min	Тур**	Max	Units
Input-Output Isolation Voltage	$(I_{I-O} \le 1 \ \mu A, t = 1 \ min.)$	V _{ISO}	5300			Vac(rms)
Isolation Resistance	(V _{I-O} = 500 VDC)	R _{ISO}	10 ¹¹			Ω
Isolation Capacitance	(f = 1 MHz)	C _{ISO}		0.5		pf

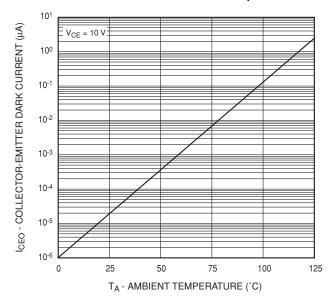
** All typicals at TA = $25^{\circ}C$



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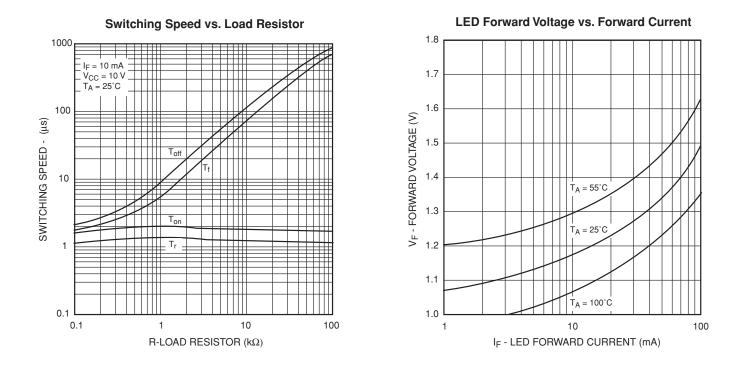


Dark Current vs. Ambient Temperature

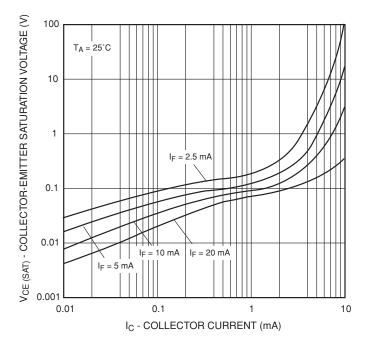




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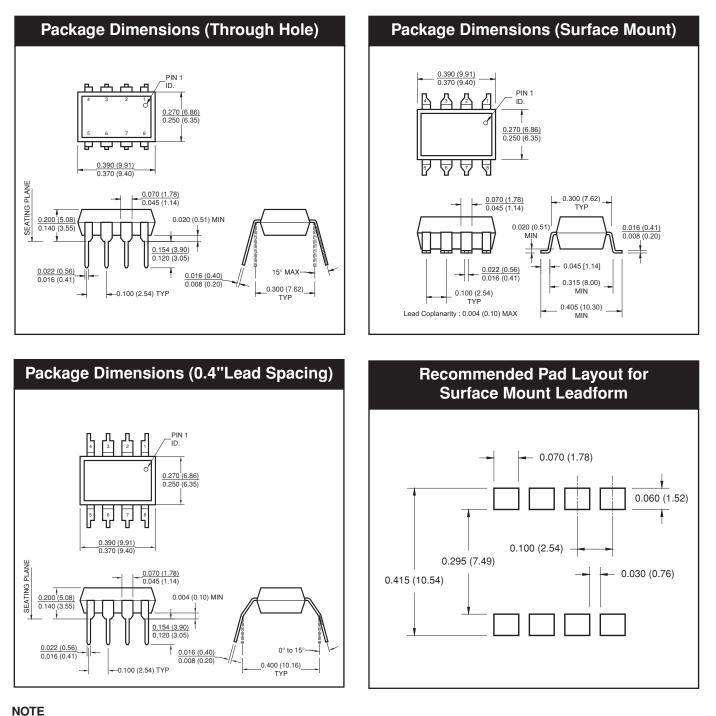


Collector-Emitter Saturation Voltage vs Collector Current





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All dimensions are in inches (millimeters)

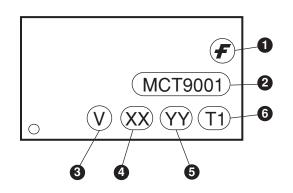


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ORDERING INFORMATION

Option	Order Entry Identifier	Description
S	.S	Surface Mount Lead Bend
SD	.SD	Surface Mount; Tape and reel
W	.W	0.4" Lead Spacing

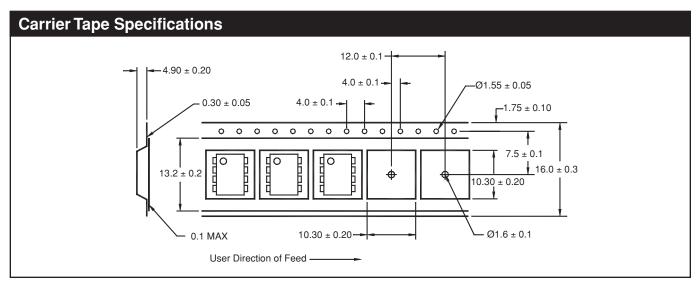
MARKING INFORMATION



Definit	Definitions		
1	1 Fairchild logo		
2	Device number		
3	VDE mark (Note: Only appears on parts ordered with VDE option – See order entry table)		
4	4 Two digit year code, e.g., '03'		
5	5 Two digit work week ranging from '01' to '53'		
6	Assembly package code		

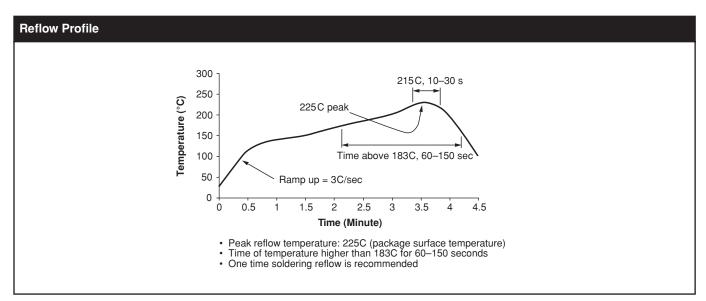


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NOTE

All dimensions are in inches (millimeters)



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EnSigna™	<i>i-Lo</i> ™	OCX™	RapidConfigure™	TruTranslation™
FACT™	ImpliedDisconnect [™]	OCXPro™	RapidConnect™	UHC™
FACT Quiet Seri		OPTOLOGIC [®]	μSerDes™	UltraFET [®]
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PRODUCT STATUS DEFINITIONS

Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	This datasheet contains preliminary data, and supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
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